



Polarized e- source
Drive Laser system

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Choice of Medium

- Wavelength determined by photocathodes
- Bandgap of GaAs based photocathodes is ~ 800 nm

Criteria	Choices			
	CW/QCW Laser Diodes	Fiber lasers (Er – doped)	OPA (See TTF laser)	Ti:Sapphire
Wavelength	Yes (limited)	Yes (frequency doubled)	Yes	Yes
Tunability	No	No	Limited	Yes
Bandwidth (pulse shaping)	No	No	Limited	Yes
Power	No	Yes	Yes	Yes
Complexity/Cost	Low	Medium	Very High	Medium
Commercial availability/interest	Yes	Yes	No	Yes (w R&D)



Laser Pulse Energy

- Determined by QE of cathode and number of required electrons
- Charge at Source: 5 nC
- Wavelength: ~ 800 nm
- Typical QE: ~ 0.5%
- Laser (pulse) energy:
$$E = \frac{n_e * h * c}{QE * \lambda}$$
- Therefore the required laser energy is ~ 1.6 μ J per micropulse + overhead (transport losses, QE decay) \rightarrow 3 – 5 μ J



ILC pulse train generation

- Pulse train generation requires mode-locked oscillator (synchronization to external RF oscillator)
- 3 MHz pulse train can be generated with cavity dumping or external pulse selection
- Ti:Sapphire guarantees sufficient bandwidth for wavelength tuning, pulse stretching and shaping



Amplification of Pulse Train (I)

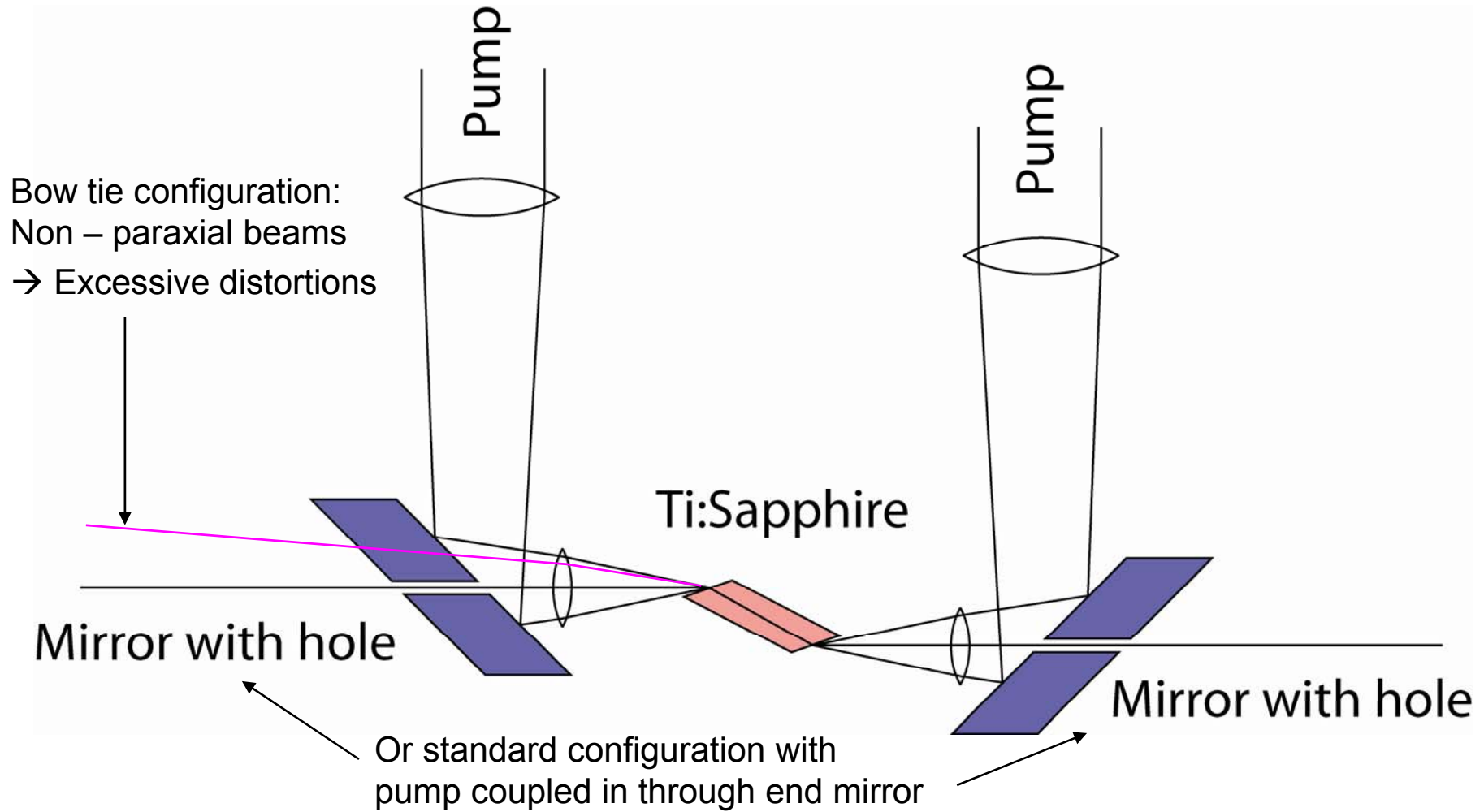
Pump Laser

- Ideal would be high pulse energy laser with 3 MHz repetition rate at correct pump wavelength
- But no reasonable pulsed pump at 3 MHz is available
 - Due to switching technology limitations
 - Highest commercial rep rate is ~ 200 kHz
- Second option is CW Amplifier pump
 - diode pumped solid state laser
 - Nd:YAG, Nd:Vanadate, Nd:YLF, Yb:YAG
 - Highest power suitable cw lasers deliver 40 W
 - Thin disk technology – advantageous heat transfer solution

Multi - Pass Amplifier Design

- Bow tie amplifier configuration
 - Passive system (+)
 - Relatively few passes (~10) (-)
 - Imperfect overlap of pump and amplified beam (-)
 - Beam distortion
- → Regenerative Amplifier ←
 - Requires switching at 3 MHz
 - loss at optical surfaces → fundamentally less efficient as bow tie amplifier
 - Many (few hundred) passes
 - Pump and amplified beam overlap

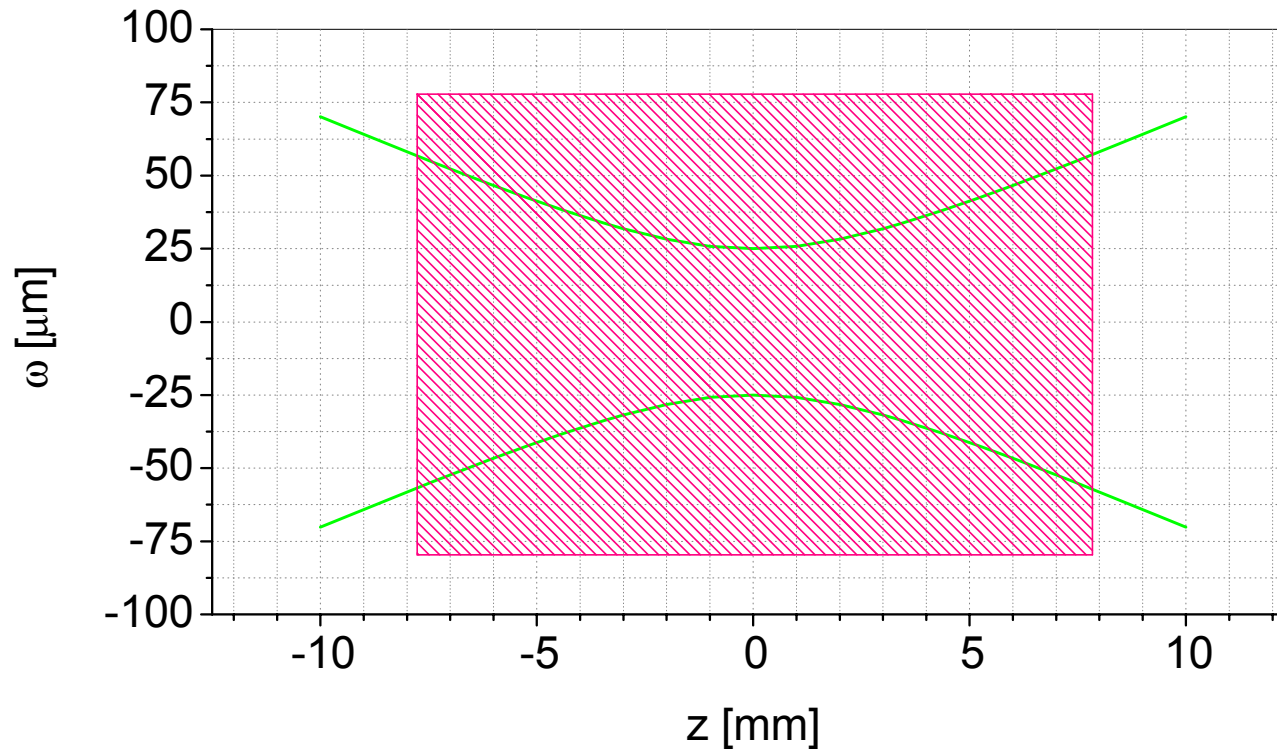
Amplifier Geometry





Amplifier Crystal Length

Rayleigh Range: $b = \frac{2\pi\omega_0^2}{\lambda}$ $\omega = \sqrt{2}\omega_0$





Cryogenic cooling of Amplifier Cell

- Issue is thermal lensing
 - 5 W pump maximum for un-cooled crystal
- Strong thermal lensing can not be compensated optically because of astigmatism ($n_e \neq n_o$)
- Solution is a cryogenically cooled amplifier cell to suppress thermal lens
 - Cryostat
 - Vacuum
 - Liquid He cooling



Pockel's Cell Technology

- Electro optical crystals also are piezo - electric crystals!

$$\Delta\phi = \left(\frac{2\pi L}{d} / \lambda \right) [-n^3 r_3 / 2 + (n-1)d_{13}] E_3$$

electro-optic coefficient

inverse piezo-electric coefficient

- At high kHz to MHz rates, piezo electric resonances occur
 - Unusable electro-optic properties
 - Catastrophic damage of crystal itself



Pockel's Cell Technology (II)

- The solution is damping of the cell
- Maintain low switching voltage by using small crystals (transverse crystal) and multiple crystals in one cell

- Double, tripple BBO
- 2- 3 mm diameter aperture



- Limited commercial availability – custom cells and drivers

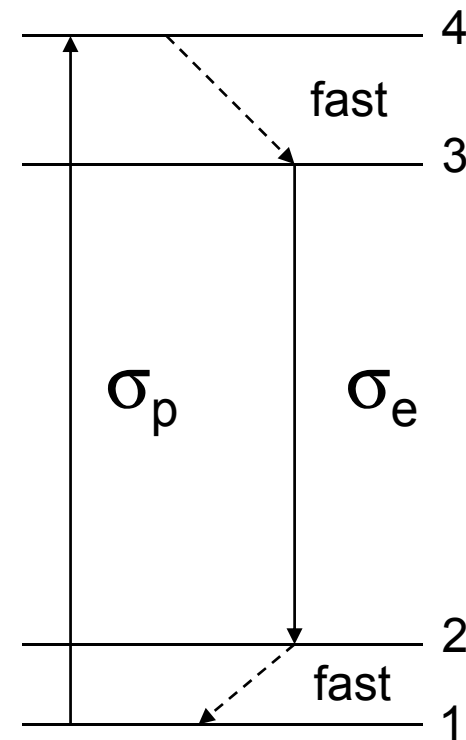
Simplified Rate Equation System

$$\frac{\partial N_1}{\partial t} = \frac{\sigma_p I_P}{h \cdot \nu_p} \bullet N_1 - \frac{N_3}{\tau_F}$$

$$N_{total} = N_1 + N_3$$

Gain Coefficient

$$G(t) = \exp[\sigma_e N_3(t)]$$

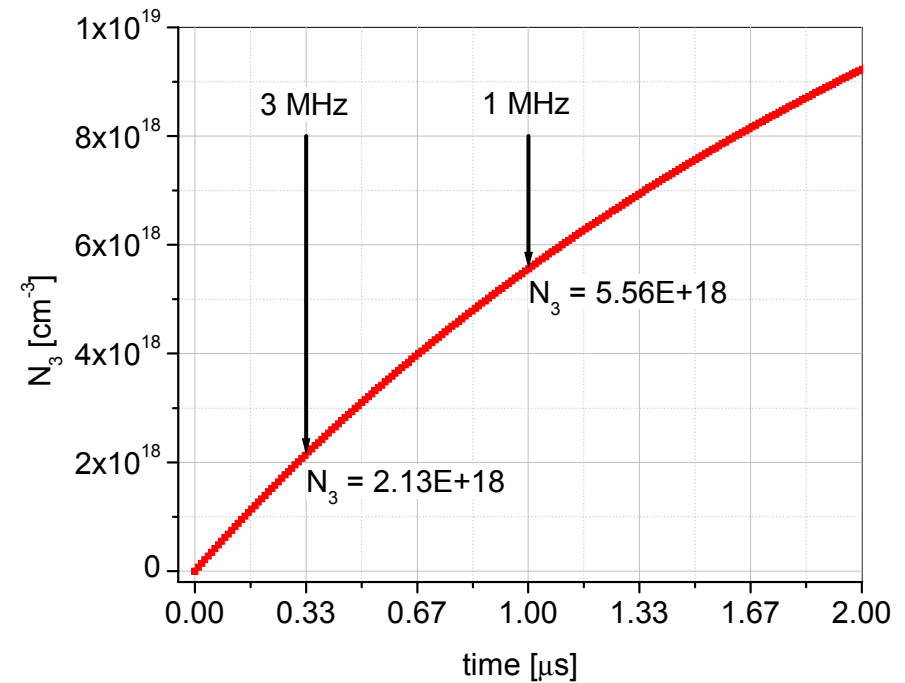


Ti:Sapphire laser physics (II)

Parameter	Value	
TiO ₂ Doping	0.2	wt %
N _{total}	6 x 10 ¹⁹	cm ⁻³
σ _p	4.9 * 10 ⁻²⁰	cm ²
σ _e	28 * 10 ⁻²⁰	cm ²
τ	3.5 * 10 ⁻⁶	s
λ _p	515	nm
λ _p	800	nm
ω ₀ = ω _p	25	μs
P _p	40	W
D	2	MW/cm ²
η	0.9	

Pump Intensity

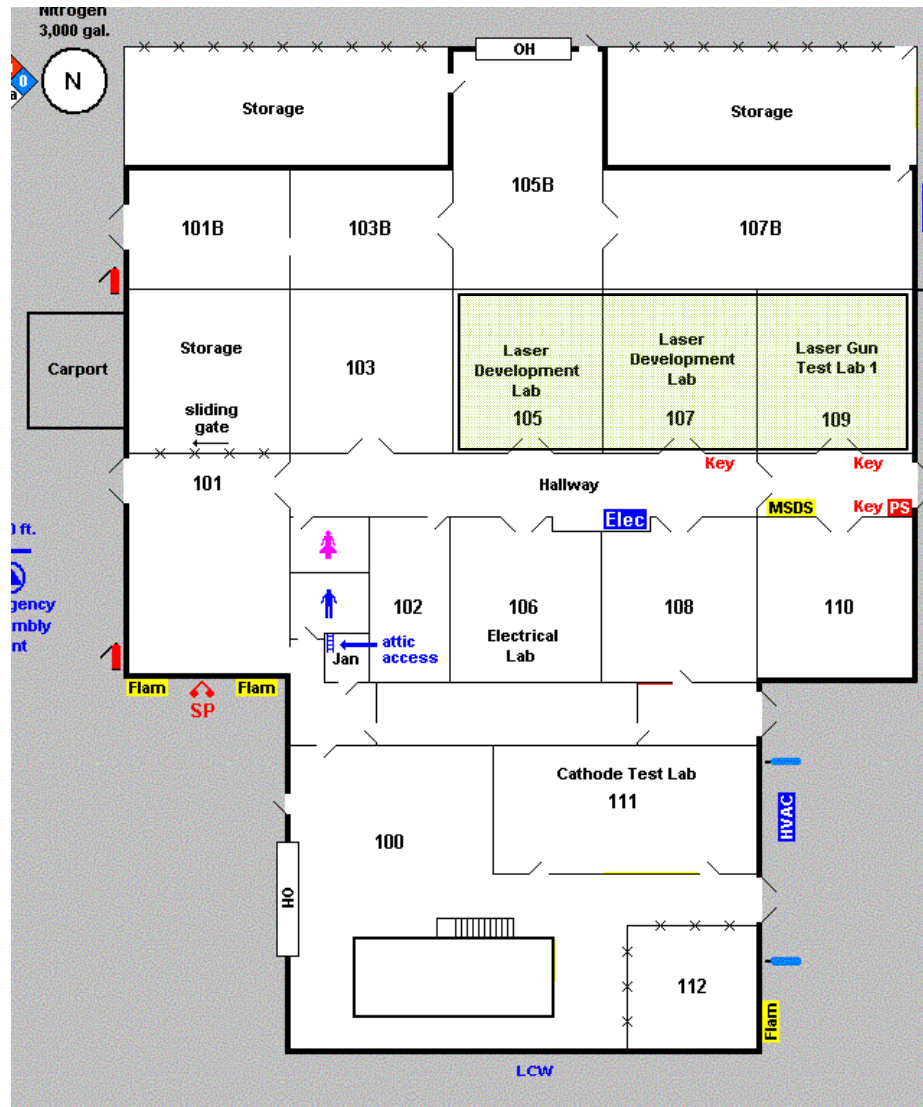
$$I_P = \eta \cdot \frac{P_p}{\pi \cdot (\omega_0^2 + \omega_p^2)}$$



$$G_{(333\text{ns})} = 1.81$$



ILC Laser Development Lab



Investments FY05-07:

- 250 k\$ HVAC system
- 175 k\$ 40 W pump laser
- 120 k\$ regenerative amplifier
(cryocooled, 3 MHz)

Current activities:

- Laser work
- Gun operation
- Photocathode development



Summary

- Laser technology suitable for the ILC source is not demonstrated or investigated in detail
- We are pushing technology in many respects
- R&D is required to confirm feasibility of our concept
- We are planning to build a 'proof of principal' laser system at SLAC
- Laser system will be used at SLAC's ITF to generate e- beam
- Laser system also needed to demonstrate photocathode performance und ILC conditions
 - Concern is surface charge limitations